

**Amendments to the Claims:**

Please cancel Claim 58 as indicated in the following listing of claims, which replaces all prior versions and listings of claims in the application.

**Listing of Claims:**

1. (Previously Presented) A method for fabricating a microelectromechanical system, the method comprising:  
producing an intermediate microstructure that includes a doped structural film, sacrificial material, and metallic material;  
dissolving the sacrificial material from the intermediate microstructure with an acid to form the microelectromechanical system; and  
suppressing dopant leaching from the doped structural film while dissolving the sacrificial material by including a nonionic detergent in the acid.
2. – 42. (Canceled).
43. (Previously Presented) The method recited in claim 1 wherein the doped structural film comprises a doped semiconductor.
44. (Previously Presented) The method recited in claim 1 wherein the doped structural film comprises doped silicon.
45. (Previously Presented) The method recited in claim 44 wherein the doped structural film comprises doped polysilicon.

46. (Previously Presented) The method recited in claim 1 wherein the metallic material comprises a material selected from the group consisting of gold, aluminum, copper, platinum, and nickel.

47. (Previously Presented) The method recited in claim 1 wherein the nonionic detergent comprises an alkyl group and a polyether-linked hydroxy group commonly linked to an aryl group.

48. (Previously Presented) The method recited in claim 1 wherein the nonionic detergent is included with a concentration relative to the acid approximately between 0.01 and 0.1 vol.%.

49. (Previously Presented) The method recited in claim 1 wherein the nonionic detergent comprises a hydrophilic moiety and a hydrophobic moiety commonly linked to an aryl group.

50. (Previously Presented) A microelectromechanical system fabricated according to the method recited in claim 1.

51. (Previously Presented) A method for fabricating a microelectromechanical system, the method comprising:

producing an intermediate microstructure that includes a doped silicon film, sacrificial material, and a metallic material selected from the group consisting of gold, aluminum, copper, platinum, and nickel;

dissolving the sacrificial material from the intermediate microstructure with an acid to form the microelectromechanical system; and

suppressing dopant leaching from the doped silicon film while dissolving the sacrificial material by including a substance comprising an alkyl group and a polyether-linked hydroxy group commonly linked to an aryl group in the acid.

52. (Previously Presented) The method recited in claim 51 wherein the doped silicon film comprises a doped polysilicon film.

53. (Previously Presented) The method recited in claim 51 wherein the substance is included with a concentration relative to the acid approximately between 0.01 and 0.1 vol.%.

54. (Previously Presented) A microelectromechanical system made according to the method recited in claim 51.

55. (Previously Presented) A method for fabricating a microelectromechanical system, the method comprising:

producing an intermediate microstructure that includes a doped silicon film, sacrificial material, and a metallic material selected from the group consisting of gold, aluminum, copper, platinum, and nickel;

dissolving the sacrificial material from the intermediate microstructure with an acid to form the microelectromechanical system; and

suppressing dopant leaching from the doped structural film while dissolving the sacrificial material by including a substance comprising a hydrophilic moiety and a hydrophobic moiety commonly linked to an aryl group in the solution.

56. (Previously Presented) The method recited in claim 55 wherein the doped silicon film comprises a doped polysilicon film.

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Examining Group

57. (Previously Presented) The method recited in claim 55 wherein the substance is included with a concentration relative to the acid approximately between 0.01 and 0.1 vol.%.

58. (Canceled).